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Vishay Semiconductors

**HALOGEN** 

FREE

# HEXFRED®, Ultrafast Soft Recovery Diode, 4 A



PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	4 A							
$V_{R}$	600 V							
V <sub>F</sub> at I <sub>F</sub>	1.4 V							
t <sub>rr</sub> (typ.)	17 ns							
$T_J$ max.	150 °C							
Package	D <sup>2</sup> PAK (TO-263AB)							
Circuit configuration	Single							

#### **FEATURES**

- Ultrafast recovery
- Ultrasoft recovery
- Very low I<sub>RRM</sub>
- Very low Q<sub>rr</sub>
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		600	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	4						
Single pulse forward current	I <sub>FSM</sub>		25	Α					
Maximum repetitive forward current	I <sub>FRM</sub>		16						
Maximum power dissipation	В	T <sub>C</sub> = 25 °C	25	W					
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	10	VV					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Cathode to anode breakdown voltage	$V_{BR}$	$I_{R} = 100 \ \mu A$	600	-	-					
Maximum forward voltage	$V_{FM}$	$I_F = 4.0 \text{ A}$		ı	1.5	1.8	V			
		$I_F = 8.0 \text{ A}$	See fig. 1	-	1.8	2.2				
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7				
Maximum reverse leakage current	I <sub>RM</sub>	$V_R = V_R$ rated	Soo fig. 2	ı	0.17	3.0	μΑ			
Maximum reverse leakage current		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	44	300				
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	ı	4.0	8.0	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	-	8.0	-	nH				

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS			
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	Vμs, V <sub>R</sub> = 30 V	-	17	-	ns		
Reverse recovery time See fig. 5, 6	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42			
500 ng. 6, 6	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	A		
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 4.0 A di <sub>F</sub> /dt = 200 A/μs	-	3.7	6.7			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	40	60	nC		
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105			
Peak rate of fall of recovery current	di <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	- A/μs		
during t <sub>b</sub> , see fig. 8	di <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	5.0	K/W				
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	r./ vv				
Maight			-	2.0	-	g				
Weight			-	0.07	-	OZ.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	HFA04TB60S							

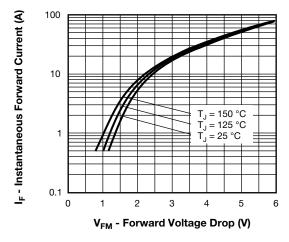


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

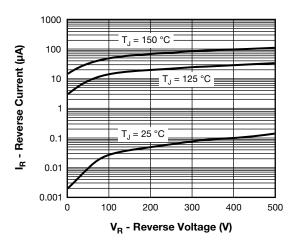


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

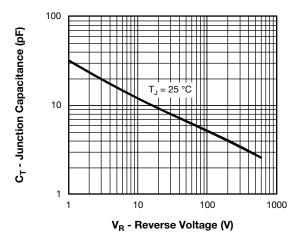


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

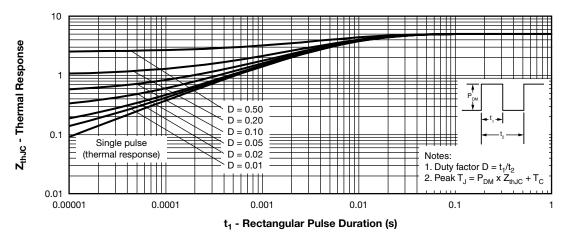


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

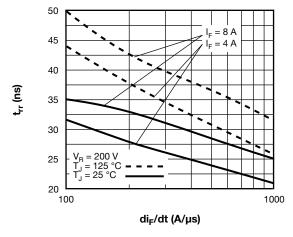


Fig. 5 - Typical Reverse Recovery Time vs. di<sub>F</sub>/dt

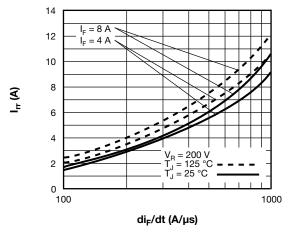
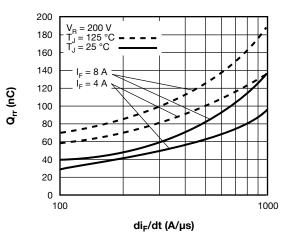


Fig. 6 - Typical Recovery Current vs. di<sub>F</sub>/dt

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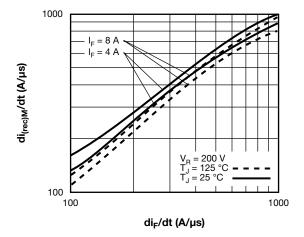
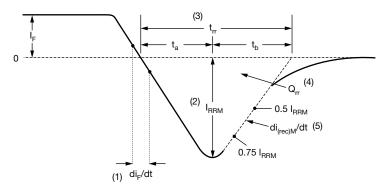


Fig. 7 - Typical Stored Charge vs. di<sub>E</sub>/dt

Fig. 8 - Typical di<sub>(rec)M</sub>/dt vs. di<sub>F</sub>/dt



- di<sub>F</sub>/dt rate of change of current through zero crossing

and  $I_{RRM}$ 

- (2)  $I_{RRM}$  peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_F$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (5)  $di_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$

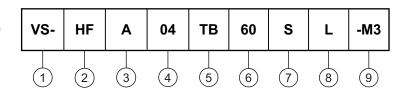
(4)  $\mathbf{Q}_{\mathrm{rr}}$  - area under curve defined by  $\mathbf{t}_{\mathrm{rr}}$ 

Fig. 9 - Reverse Recovery Waveform and Definitions



## **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - HEXFRED® family

Process designator: A = electron irradiated

4 - Current rating (04 = 4 A)

5 - Package outline (TB = TO-220, 2 leads)

Voltage rating (60 = 600 V)

7 -  $S = D^2PAK (TO-263AB)$ 

• None = tube (50 pieces)

• L = tape and reel (left oriented)

• R = tape and reel (right oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-HFA04TB60S-M3	50	Antistatic plastic tube							
VS-HFA04TB60SL-M3	800	13" diameter reel							
VS-HFA04TB60SR-M3	800	13" diameter reel							

LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96164</u>							
Part marking information	www.vishay.com/doc?95444						
Packaging information	www.vishay.com/doc?96424						



## D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES		STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3 0.25 BSC 0.010 BS		BSC			
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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